85V N-Channel Enhancement Mode MOSFET

MAIN CHARACTERISTICS

I_D	120A
V_{DSS}	85V
R_{DSON}-typ(@V_{GS}=10V)	、 5.0mq **(Type:4.5 mΩ)**

Features

- YFW-SGT technology
- Ultra-low RDS(ON)
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- Halog en-r e an RoHS-com l ant

A IC AT

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- 100 an ntn Telecom Ind t al tomat on CE l at

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition

YFWG1

YFWG120N085AD

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